

Electronic and magnetic properties of defective and Fe-doped InS monolayer adjusted by hole doping: A first-principles study

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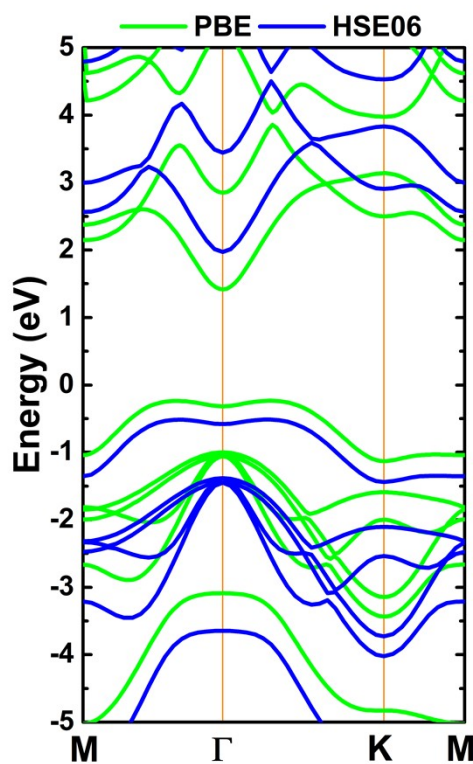


Figure S1: Electronic band structure of InS monolayer calculated with PBE and HSE06 functionals (The Fermi level is set to 0 eV).